

hole of a separable pattern on a drain electrode of a TFT is formed by plainly applying a photosensitive insulating resin so that it may dissolve difference in level caused by a gate electrode wiring, source electrode wiring, and the TFT, and conducting exposure and development while changing exposure amount. The exposure of the insulating resin is conducted through divisional exposure in which the inseparable pattern and the separable pattern are arranged on different masks, and the inseparable pattern is exposed by a predetermined exposure amount of 20 to 80 % of an exposure amount for the separable pattern.--

REMARKS

At the time of the Office Action dated September 16, 2002, claims 1-17 were pending and rejected in this application. Claims 2-5 have been amended, and claims 1, 7-12 and 14-15 have been cancelled. Care has been exercised to avoid the introduction of new matter. Specifically, claims 2 and 3 have been placed in independent form, claim 4 has been amended and claim 18 added to address a dependency issue arising from the cancellation of claim 1. Applicants submit that the present Amendment does not generate any new matter issue.

In the first enumerated paragraph of the Office Action, the Examiner required a new Abstract be provided. By this Amendment, a new Abstract has been submitted.

Claims 3 and 8-12 are rejected under the second paragraph of 35 U.S.C. § 112

In the third enumerated paragraph of the Office Action, the Examiner identified a perceived informality with regard to claim 8 generating an antecedent basis issue. Claim 8 has